

Customer No.: 31561
Application No.: 10/605,122
Docket No.: 9165-US-PA-OP

Specification Amendment

Please replace paragraph [0031] of the disclosure with the following paragraph:

[0031] Referring to Fig. 2D, a lightly doped drain (LDD) region 210 is formed in the strained silicon layer 204 at both sides of the gate structure 208. For example, once the gate structure 208 is established, the gate structure 208 serves to mask an lightly doped drain (LDD) implant into a certain thickness of the strained silicon layer 204 at both sides of the gate structure 208 to form the LDD region 210. Alternatively, the lightly doped region 210 is formed occupying the entire thickness of the strained silicon layer 204 at both sides of the gate structure 208 as shown in Figure 3A. The ~~LDD~~-LDD implant comprises, for example, n-type species, such as, arsenic ions, for forming an NMOS transistor. Further, the dosage and the implant energy are chosen such that the LDD region 210 is shallower than and of lighter concentration than the subsequent source/drain region.

BEST AVAILABLE COPY

**This Page is Inserted by IFW Indexing and Scanning
Operations and is not part of the Official Record**

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images include but are not limited to the items checked:

- BLACK BORDERS**
- IMAGE CUT OFF AT TOP, BOTTOM OR SIDES**
- FADED TEXT OR DRAWING**
- BLURRED OR ILLEGIBLE TEXT OR DRAWING**
- SKEWED/SLANTED IMAGES**
- COLOR OR BLACK AND WHITE PHOTOGRAPHS**
- GRAY SCALE DOCUMENTS**
- LINES OR MARKS ON ORIGINAL DOCUMENT**
- REFERENCE(S) OR EXHIBIT(S) SUBMITTED ARE POOR QUALITY**
- OTHER:** _____

IMAGES ARE BEST AVAILABLE COPY.

As rescanning these documents will not correct the image problems checked, please do not report these problems to the IFW Image Problem Mailbox.